Solid State Devices, Inc.	SSR2010CTS1
14701 Firestone Blvd * La Mirada, CA 90638 Phone: (562) 404-4474 * Fax: (562) 404-1773 ssdi@ssdi-power.com * www.ssdi-power.com Designer's Data Sheet Part Number / Ordering Information ^{1/} SSR2010 CT <u>S1</u> L Screening ^{2/} = Not Screened	20 AMP 100 VOLTS POSITIVE CENTERTAP SCHOTTKY RECTIFIER
TX = TX Level TXV = TXV Level S = S Level L Package S1 = SMD1	 FEATURES: PIV: 100 Volts Low Forward Voltage Drop Low Reverse Leakage Hermetically Sealed Power Surface Mount Package Guard Ring for Overvoltage Protection Eutectic Die Attach 175 °C Operating Junction Temperature TX, TXV, or Space Level Screening Available

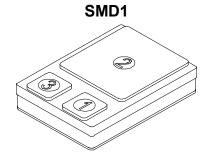
MAXIMUM RATINGS			
RATING	SYMBOL	VALUE	UNIT
Peak Repetitive Reverse Voltage SSR2010CT and DC Blocking Voltage	V _{RRM} V _{RWM} V _R	100	Volts
Average Rectified Output Current ^{3/} (Resistive Load, 60Hz, Sine Wave, TA=25°C)	Ι _ο	20	Amps
Peak Surge Current ^{$\underline{3}$/} (8.3 ms Pulse, Half Sine Wave superimposed on I ₀ , allow junction to reach equilibrium between pulses, TA=25°C)	I _{FSM}	300	Amps
Operating and Storage Temperature	T _{OP} & T _{STG}	-65 to +175	°C
Maximum Thermal Resistance ^{3/} Junction to Case	R _{ejc}	0.8	°C/W

Note:

 $\underline{1}$ / For ordering information, price, and availability, contact factory.

 $\underline{2}$ / Screening based on MIL-PRF-19500. Screening flows available on request.

3/ Both legs tied together.



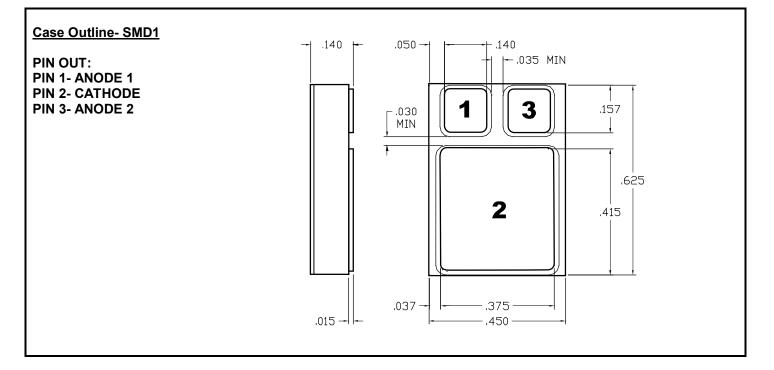
NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.	DATA SHEET #: RS0067E
--	-----------------------



Solid State Devices, Inc. 14701 Firestone Blvd * La Mirada, CA 90638 Phone: (562) 404-4474 * Fax: (562) 404-1773 ssdi@ssdi-power.com * www.ssdi-power.com

SSR2010CTS1

ELECTRICAL CHARACTERISTICS (Per Leg)			
CHARACTERISTICS	SYMBOL	MAXIMUM	UNIT
Instantaneous Forward Voltage Drop ($I_F = 3 \text{ Adc}, T_A = 25^{\circ}\text{C}, \text{ Pulse}$) ($I_F = 5 \text{ Adc}, T_A = 25^{\circ}\text{C}, \text{ Pulse}$) ($I_F = 10 \text{ Adc}, T_A = 25^{\circ}\text{C}, \text{ Pulse}$)	V _{F1} V _{F2} V _{F3}	0.68 0.7 0.77	Vdc
Instantaneous Forward Voltage Drop ($I_F = 5 \text{ Adc}, T_A = -55^{\circ}\text{C}, \text{ Pulse}$)	V _{F4}	0.84	Vdc
Reverse Leakage Current (Rated V _R , T _A = 25°C, Pulse)	I _{R1}	100	μA
Reverse Leakage Current (Rated V _R , T _A = 100°C, Pulse)	I _{R2}	5	mA
Junction Capacitance (V_R = 10 Vdc, T_A = 25°C, f = 1 MHz)	CJ	400	pF



NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.	DATA SHEET #: RS0067E	DOC	
--	-----------------------	-----	--